

Preliminary

Essential:

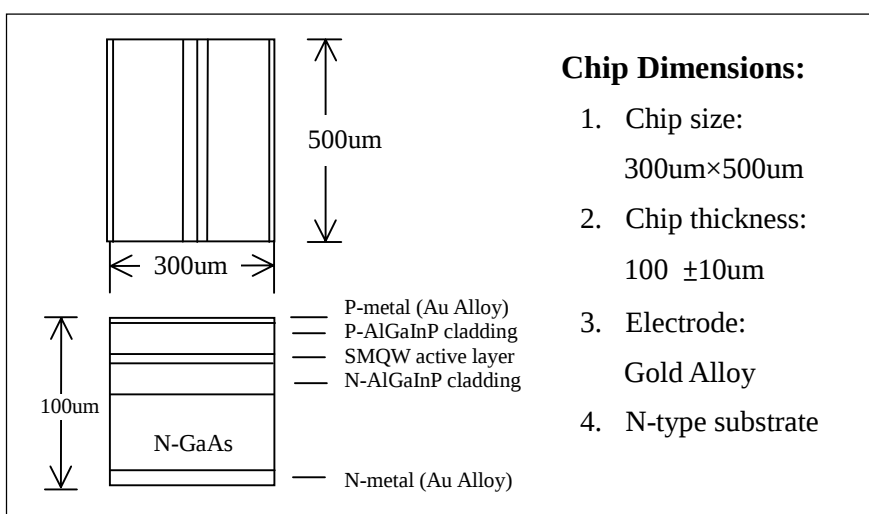
- Visible Laser
- AlGaInP/GaAs
- MOVPE Process
- Strained MQW

Product Description:

UEL-L65-DB is a short wavelength red LD chips fabricated from aluminum gallium indium phosphide (AlGaInP) MOVPE technology. The low threshold current and short wavelength are achieved by the use of strained multiple quantum well active layer structure. Its high temperature characteristics could be operated at 7mW within 70°C. UEL-L65-DB AlGaInP LD chips is ideal for use as a light source for optical pickup head and various other types of optical systems.

Great Performance:

- Short Wavelength:
650nm(typ.)
- Output Power:
7mW CW
- High Temperature:
70 °C
- 100% Probing
- Degradation Tests
- Optical Pickup Head



Applications

Absolute Maximum Ratings (Tc=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Rated Optical Power	P_o	7	mW
Operating Temperature	T_{op}	-10~70	°C
Storage Temperature	T_{stg}	-20~85	°C
Reverse Voltage	V_{RLD}	2	V

Optical & Electrical Characteristics (Tc=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION
Threshold Current	I_{th}	-	25	35	mA	CW
Operation Current	I_{op}	-	40	55	mA	$P_o=5mW$
Operation Voltage	V_{op}	-	2.2	2.5	V	$P_o=5mW$
Lasing Wavelength	λ_p	645	650	660	nm	$P_o=5mW$
Beam Divergence	$\Theta_{ }$	-	7		deg	$P_o=5mW$
	$\Theta_{\perp}$	-	30		deg	FWHM

- I_{op} is measured on bare chips with UEC's tester.
- Bonding Condition Note: Die-bonding on a good heat sink.

Contact us:

9F, NO 10, Li-Hsin Rd.
Science-Based Industrial Park,
Hsinchu, Taiwan, R.O.C.
TEL: 886-3-567-8000
FAX: 886-3-567-8753
sales@uec.com.tw